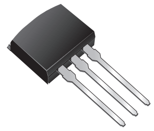
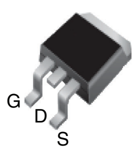
Power MOSFET

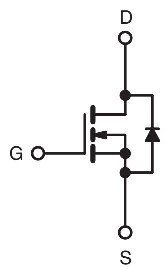
PRODUCT SUMMARY		
V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	2.2
Q_g (Max.) (nC)	31	
Q_{gs} (nC)	4.6	
Q_{gd} (nC)	17	
Configuration	Single	

I2PAK (TO-262)



D2PAK (TO-263)





N-Channel MOSFET

FEATURES

- Surface Mount (IRFBC30S, SiHFBC30S)
- Low-Profile Through-Hole (IRFBC30L, SiHFBC30L)
- Available in Tape and Reel (IRFBC30S, SiHFBC30S)
- Dynamic dV/dt Rating
- 150 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead (Pb)-free Available

Pb Available
RoHS* COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.
The D2PAK is a surface mount power package capable of the accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D2PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application. The through-hole version (IRFBC30L, SiHFBC30L) is a available for low-profile applications.

ORDERING INFORMATION			
Package	D2PAK (TO-263)	D2PAK (TO-263)	I2PAK (TO-262)
Lead (Pb)-free	IRFBC30SPbF	IRFBC30STRLPbF[a]	IRFBC30LPbF
	SiHFBC30S-E3	SiHFBC30STL-E3[a]	SiHFBC30L-E3
SnPb	IRFBC30S	-	IRFBC30L
	SiHFBC30S	-	SiHFBC30L

Note
a. See device orientation.

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

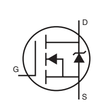
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current[e]	V_{GS} at 10 V	T_C = 25 °C	I_D	3.6	A
		T_C = 100 °C		2.3	
Pulsed Drain Current[a, e]			I_{DM}	14	
Linear Derating Factor				0.59	W/°C
Single Pulse Avalanche Energy[b, e]			E_{AS}	290	mJ
Avalanche Current[a]			I_{AR}	3.6	A
Repetiitive Avalanche Energy[a]			E_{AR}	7.4	mJ
Maximum Power Dissipation		T_A = 25 °C	P_D	3.1	W
		T_C = 25 °C		74	
Peak Diode Recovery dV/dt[c, e]			dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[d]	

Notes
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 41 mH, R_G = 25 Ω, I_{AS} = 3.6 A (see fig. 12).
c. $I_{SD} \le 3.6$ A, dI/dt ≤ 60 A/μs, $V_{DD} \le V_{DS}$, $T_J \le 150$ °C.
d. 1.6 mm from case.
e. Uses IRFBC30/SiHFBC30 data and test conditions.
* Pb containing terminations are not RoHS compliant, exemptions may apply

WORK-IN-PROGRESS

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient (PCB Mounted, steady-state)[a]	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note
a. When mounted on 1" square PCB (FR-4 or G-10 material).
For recommended footprint and soldering techniques refer to application note #AN-994.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA[c]		-	0.62	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V		-	-	100	µA
		V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 °C		-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 2.2 A[b]	-	-	2.2	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 2.2 A[c]		2.5	-	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5[c]		-	660	-	pF
Output Capacitance	C_{oss}			-	86	-	
Reverse Transfer Capacitance	C_{rss}			-	19	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 3.6 A, V_{DS} = 360 V, see fig. 6 and 13[b, c]	-	-	31	nC
Gate-Source Charge	Q_{gs}			-	-	4.6	
Gate-Drain Charge	Q_{gd}			-	-	17	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 300 V, I_D = 3.6 A, R_G = 12 Ω, R_D = 82 Ω, see fig. 10[b, c]		-	11	-	ns
Rise Time	t_r			-	13	-	
Turn-Off Delay Time	$t_{d(off)}$			-	35	-	
Fall Time	t_f			-	14	-	
Internal Source Inductance	L_S	Between lead, and center of die contcat		-	7.5	-	nH
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	3.6	A
Pulsed Diode Forward Current[a]	I_{SM}			-	-	14	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 3.6 A, V_{GS} = 0 V[b]		-	-	1.6	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 3.6 A, dI/dt = 100 A/µs[b, c]		-	370	810	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	2.0	4.2	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.
c. Uses IRFBC30/SiHFBC30 data and test conditions.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

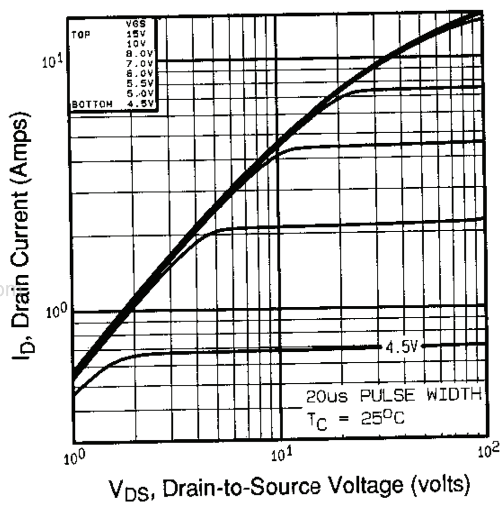


Fig. 1 - Typical Output Characteristics

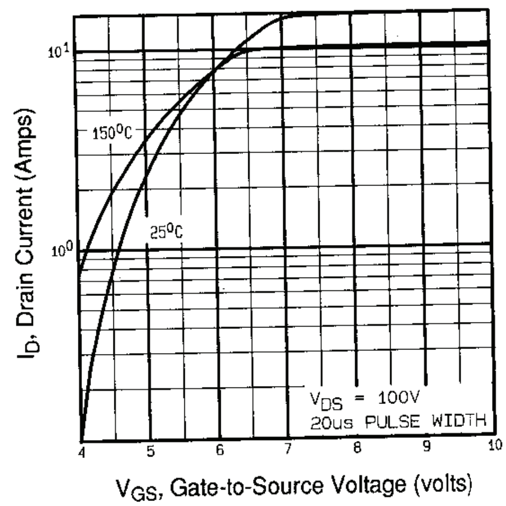


Fig. 3 - Typical Transfer Characteristics

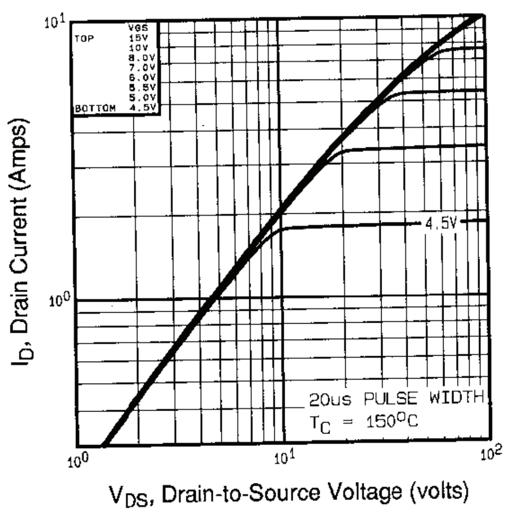


Fig. 2 - Typical Output Characteristics

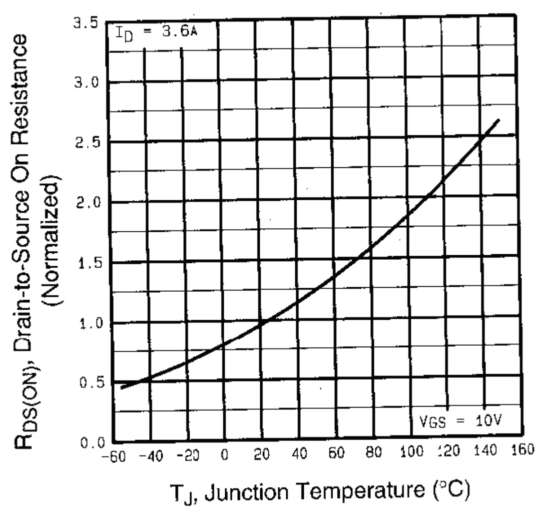


Fig. 4 - Normalized On-Resistance vs. Temperature

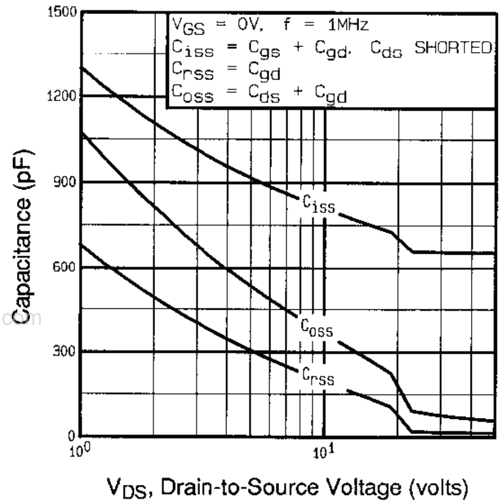


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

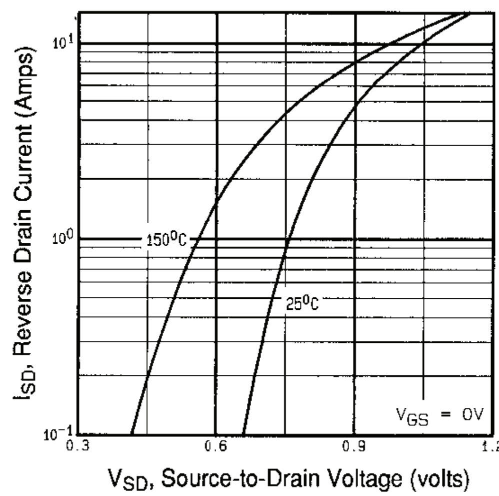


Fig. 7 - Typical Source-Drain Diode Forward Voltage

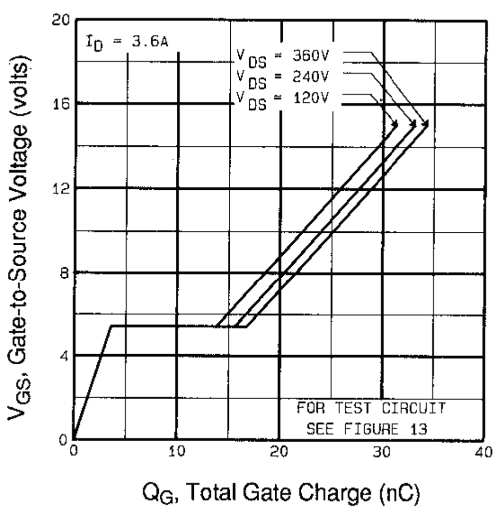


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

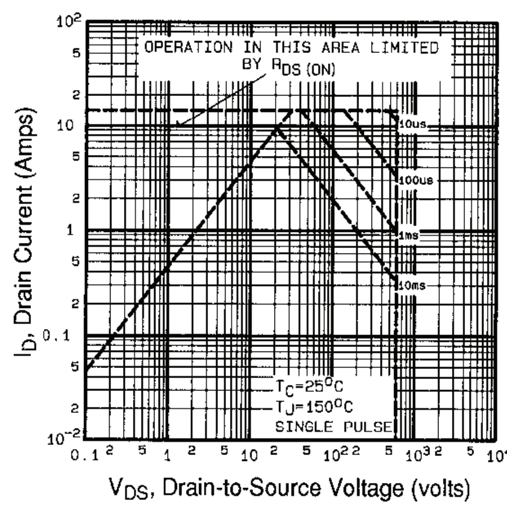


Fig. 8 - Maximum Safe Operating Area

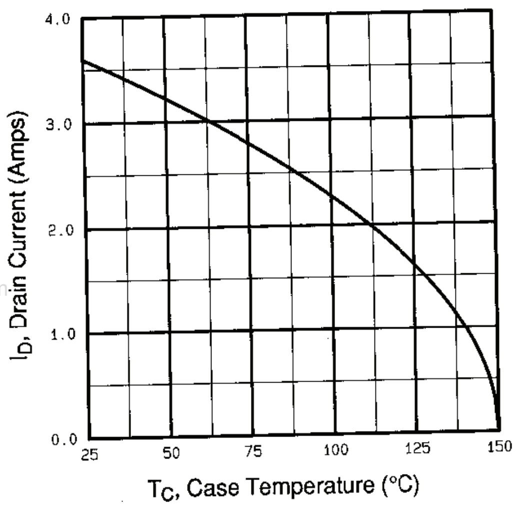


Fig. 9 - Maximum Drain Current vs. Case Temperature

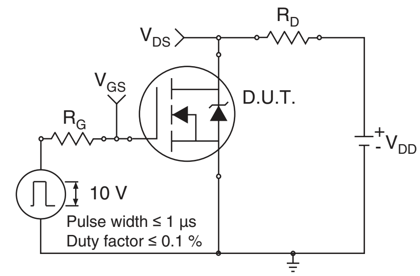


Fig. 10a - Switching Time Test Circuit

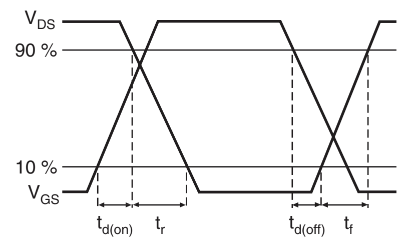


Fig. 10b - Switching Time Waveforms

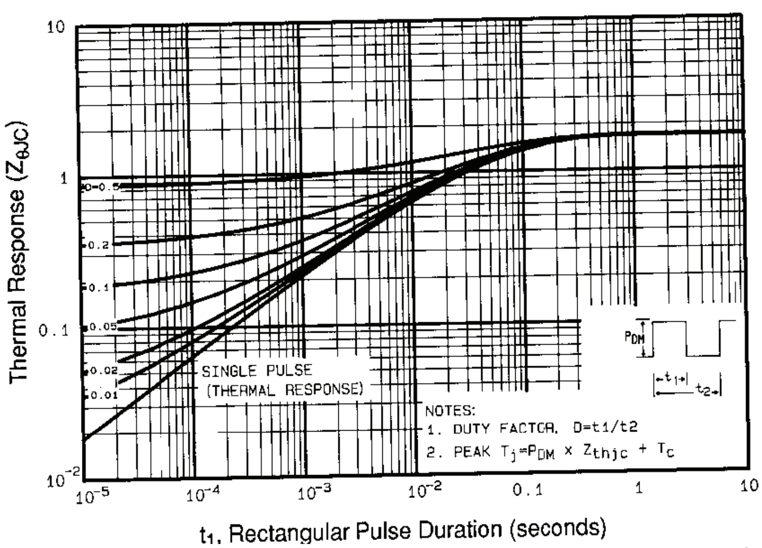


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

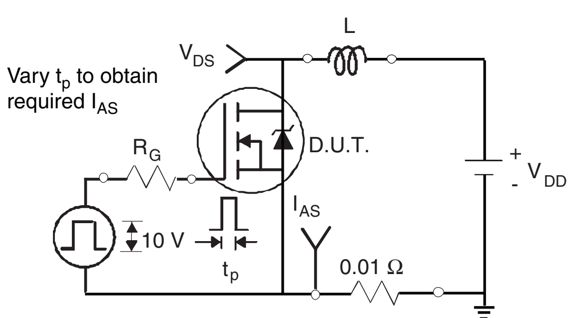


Fig. 12a - Unclamped Inductive Test Circuit

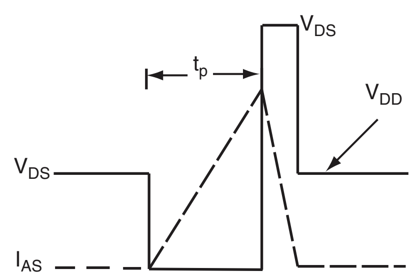


Fig. 12b - Unclamped Inductive Waveforms

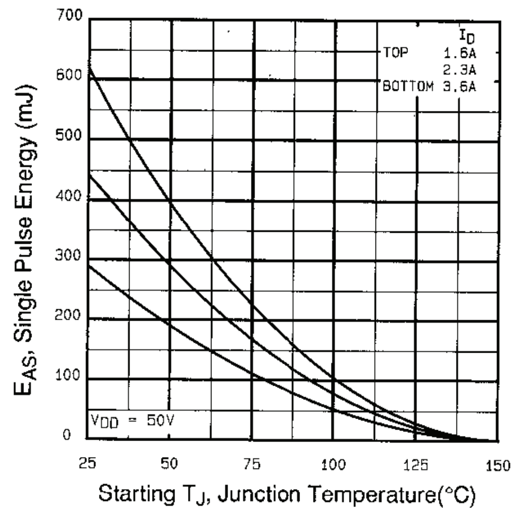


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

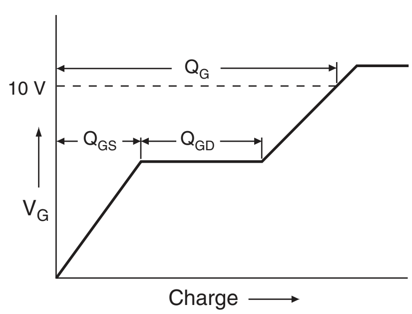


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

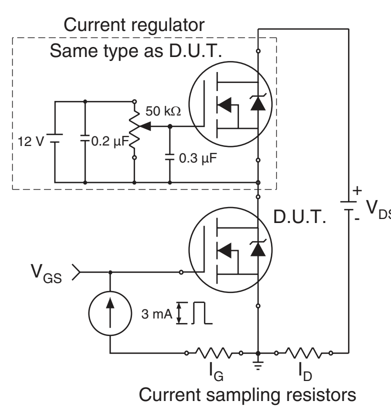
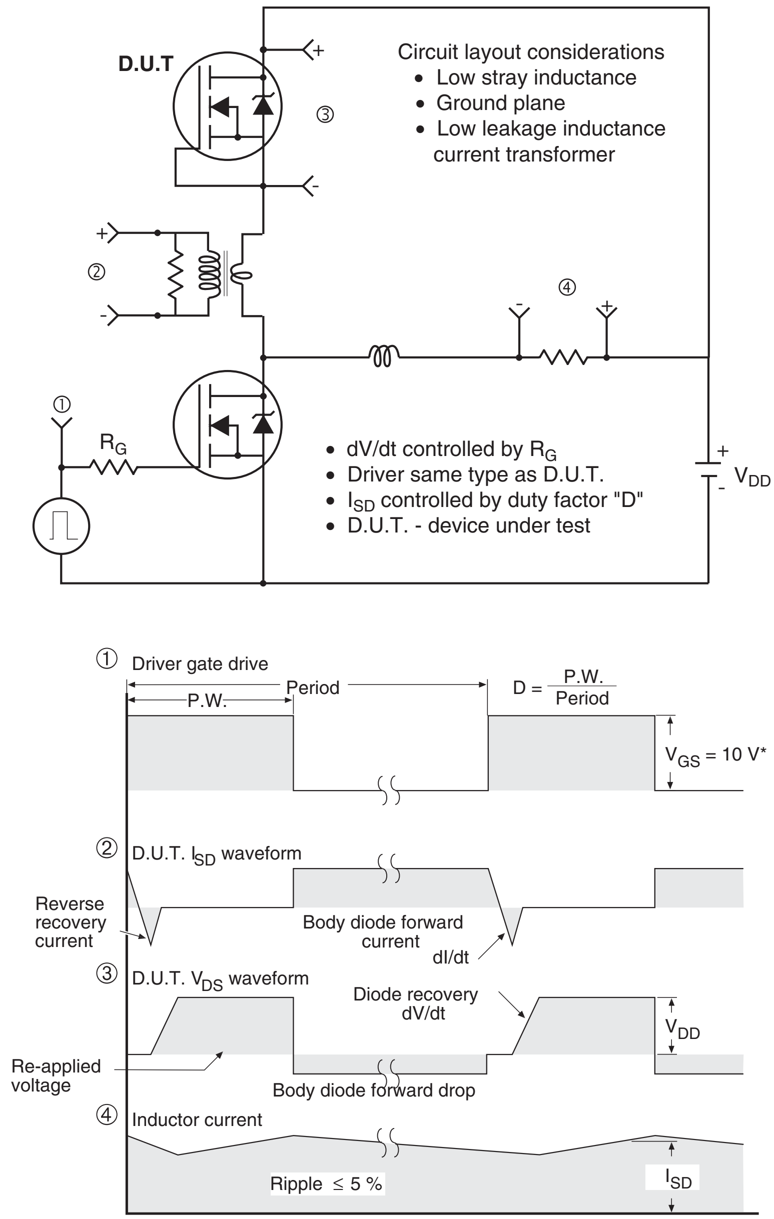


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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